

CR25RM-12D

Thyristor

Medium Power Use

REJ03G1716-0100

Rev.1.00

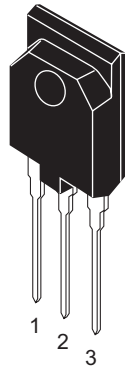
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Features

- $I_{T(AV)}$: 25 A
- V_{DRM} : 600 V
- I_{GT} : 30 mA
- V_{ISO} : 2000 V
- Insulated Type
- Planar Passivation Type
- The product guaranteed maximum junction temperature of 150°C

Outline

RENESAS Package code: PRSS0003ZA-A
(Package name: TO-3PFM)



1. Cathode
2. Anode
3. Gate

Applications

Switching mode power supply, motor control, heater control, and other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak reverse voltage	V_{RRM}	600	V
Non-repetitive peak reverse voltage	V_{RSM}	720	V
DC reverse voltage	$V_{R(DC)}$	480	V
Repetitive peak off-state voltage	V_{DRM}	600	V
DC off-state voltage	$V_{D(DC)}$	480	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	39.3	A	
Average on-state current	$I_{T(AV)}$	25	A	Commercial frequency, sine half wave 180° conduction, $T_c = 61^\circ\text{C}$
Surge on-state current	I_{TSM}	360	A	50 Hz sine half wave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	648	A^2s	Value corresponding to 1 cycle of half wave 50 Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate forward voltage	V_{FGM}	6	V	
Peak gate reverse voltage	V_{RGM}	10	V	
Peak gate forward current	I_{FGM}	2	A	
Junction temperature	T_j	- 40 to +150	$^\circ\text{C}$	
Storage temperature	T_{stg}	- 40 to +150	$^\circ\text{C}$	
Mass	—	5.2	g	Typical value
Isolation voltage	Viso	2000	V	$T_a = 25^\circ\text{C}$, AC 1 minute, each terminal to case

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak reverse current	I_{RRM}	—	—	2.0/5.0	mA	$T_j = 125^\circ\text{C}/150^\circ\text{C}$, V_{RRM} applied
Repetitive peak off-state current	I_{DRM}	—	—	2.0/5.0	mA	$T_j = 125^\circ\text{C}/150^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.6	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 40\text{ A}$, instantaneous value
Gate trigger voltage	V_{GT}	—	—	1.5	V	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 1\text{ A}$
Gate non-trigger voltage	V_{GD}	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C}/150^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Gate trigger current	I_{GT}	—	—	30	mA	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $I_T = 1\text{ A}$
Holding current	I_H	—	15	—	mA	$T_j = 25^\circ\text{C}$, $V_D = 12\text{ V}$
Thermal resistance	$R_{th(j-c)}$	—	—	1.6	$^\circ\text{C}/\text{W}$	Junction to case ^{Note1}

Notes: 1. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is $0.5^\circ\text{C}/\text{W}$.